
# PSMN6R0-30YLD

## N-channel 30 V, 6.0 mΩ logic level MOSFET in LFPAK56 using NextPowerS3 Technology

**10 October 2013** **Product data sheet**

## 1. General description

Logic level gate drive N-channel enhancement mode MOSFET in LFPAK56 package. NextPowerS3 portfolio utilising NXP's unique "SchottkyPlus" technology delivers high efficiency, low spiking performance usually associated with MOSFETs with an integrated Schottky or Schottky-like diode but without problematic high leakage current. NextPowerS3 is particularly suited to high efficiency applications at high switching frequencies.

## 2. Features and benefits

- Ultra low $Q_G$, $Q_{GD}$ and $Q_{OSS}$ for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery; s-factor > 1
- Low spiking and ringing for low EMI designs
- Unique "SchottkyPlus" technology; Schottky-like performance with < 1 µA leakage at 25 °C
- Optimised for 4.5 V gate drive
- Low parasitic inductance and resistance
- High reliability clip bonded and solder die attach Power SO8 package; no glue, no wire bonds, qualified to 175 °C
- Wave solderable; exposed leads for optimal visual solder inspection

## 3. Applications

- On-board DC-to-DC solutions for server and telecommunications
- Secondary-side synchronous rectification in telecommunication applications
- Voltage regulator modules (VRM)
- Point-of-Load (POL) modules
- Power delivery for V-core, ASIC, DDR, GPU, VGA and system components
- Brushed and brushless motor control

## 4. Quick reference data

**Table 1. Quick reference data**

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| $V_{DS}$ | drain-source voltage | 25 °C ≤ $T_j$ ≤ 175 °C | | - | - | 30 | V |
| $I_D$ | drain current | $T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; Fig. 1 | | - | - | 66 | A |
| $P_{tot}$ | total power dissipation | $T_{mb}$ = 25 °C; Fig. 2 | | - | - | 47 | W |

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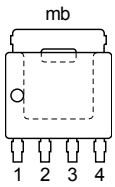
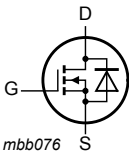
| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| $T_j$ | junction temperature | | | -55 | - | 175 | °C |
| **Static characteristics** | | | | | | | |
| $R_{DSon}$ | drain-source on-state resistance | $V_{GS}$ = 4.5 V; $I_D$ = 15 A; $T_j$ = 25 °C; Fig. 10 | | - | 6.7 | 8.35 | mΩ |
| | | $V_{GS}$ = 10 V; $I_D$ = 15 A; $T_j$ = 25 °C; Fig. 10 | | - | 5 | 6 | mΩ |
| **Dynamic characteristics** | | | | | | | |
| $Q_{GD}$ | gate-drain charge | $V_{GS}$ = 4.5 V; $I_D$ = 15 A; $V_{DS}$ = 15 V; Fig. 12; Fig. 13 | | - | 1.8 | - | nC |
| $Q_{G(tot)}$ | total gate charge | $V_{GS}$ = 4.5 V; $I_D$ = 15 A; $V_{DS}$ = 15 V; Fig. 12; Fig. 13 | | - | 6.5 | - | nC |
| **Source-drain diode** | | | | | | | |
| S | softness factor | $I_S$ = 15 A; $V_{GS}$ = 0 V; $dI_S/dt$ = -100 A/µs; $V_{DS}$ = 15 V; Fig. 16 | | - | 1.2 | - | |

## 5. Pinning information

**Table 2. Pinning information**

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|---|---|---|---|---|
| 1 | S | source |   **LFPAK56; Power-SO8 (SOT669)** |   |
| 2 | S | source | | |
| 3 | S | source | | |
| 4 | G | gate | | |
| mb | D | mounting base; connected to drain | | |

## 6. Ordering information

**Table 3. Ordering information**

| Type number | Package | | |
|---|---|---|---|
| | Name | Description | Version |
| PSMN6R0-30YLD | LFPAK56; Power-SO8 | Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads | SOT669 |

## 7. Marking

**Table 4. Marking codes**

| Type number | Marking code |
|---|---|
| PSMN6R0-30YLD | 6D030L |

# 8. Limiting values

**Table 5. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|---|---|---|---|---|---|---|
| $V_{DS}$ | drain-source voltage | 25 °C ≤ $T_j$ ≤ 175 °C | | - | 30 | V |
| $V_{DGR}$ | drain-gate voltage | 25 °C ≤ $T_j$ ≤ 175 °C; $R_{GS}$ = 20 kΩ | | - | 30 | V |
| $V_{GS}$ | gate-source voltage | | | -20 | 20 | V |
| $I_D$ | drain current | $V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; Fig. 1 | | - | 66 | A |
| | | $V_{GS}$ = 10 V; $T_{mb}$ = 100 °C; Fig. 1 | | - | 46 | A |
| $I_{DM}$ | peak drain current | pulsed; $t_p$ ≤ 10 µs; $T_{mb}$ = 25 °C; Fig. 3 | | - | 263 | A |
| $P_{tot}$ | total power dissipation | $T_{mb}$ = 25 °C; Fig. 2 | | - | 47 | W |
| $T_{stg}$ | storage temperature | | | -55 | 175 | °C |
| $T_j$ | junction temperature | | | -55 | 175 | °C |
| $T_{sld(M)}$ | peak soldering temperature | | | - | 260 | °C |
| $V_{ESD}$ | electrostatic discharge voltage | HBM | | 250 | - | V |
| **Source-drain diode** | | | | | | |
| $I_S$ | source current | $T_{mb}$ = 25 °C | | - | 39 | A |
| $I_{SM}$ | peak source current | pulsed; $t_p$ ≤ 10 µs; $T_{mb}$ = 25 °C | | - | 263 | A |
| **Avalanche ruggedness** | | | | | | |
| $E_{DS(AL)S}$ | non-repetitive drain-source avalanche energy | $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 15 A; $V_{sup}$ ≤ 30 V; $R_{GS}$ = 50 Ω; unclamped; $t_p$ = 158 µs | [1] | - | 46 | mJ |

[1] Protected by 100% test

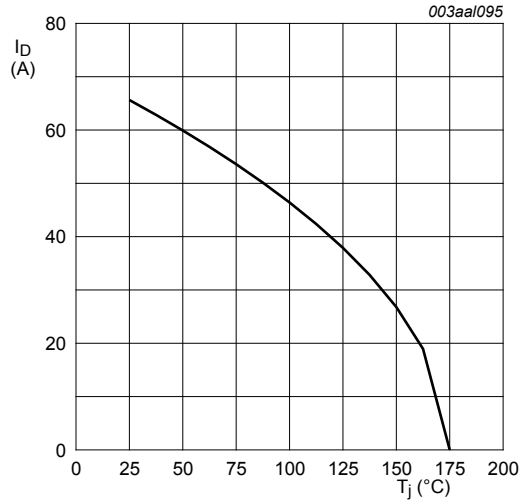



**Fig. 1. Continuous drain current as a function of mounting base temperature**

$$V_{GS} \geq 10V$$

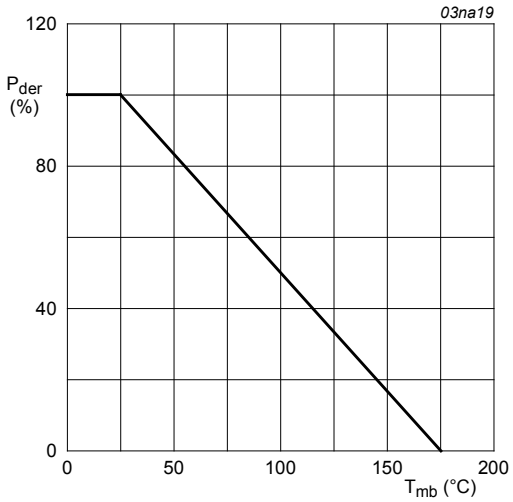



**Fig. 2. Normalized total power dissipation as a function of mounting base temperature**

$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

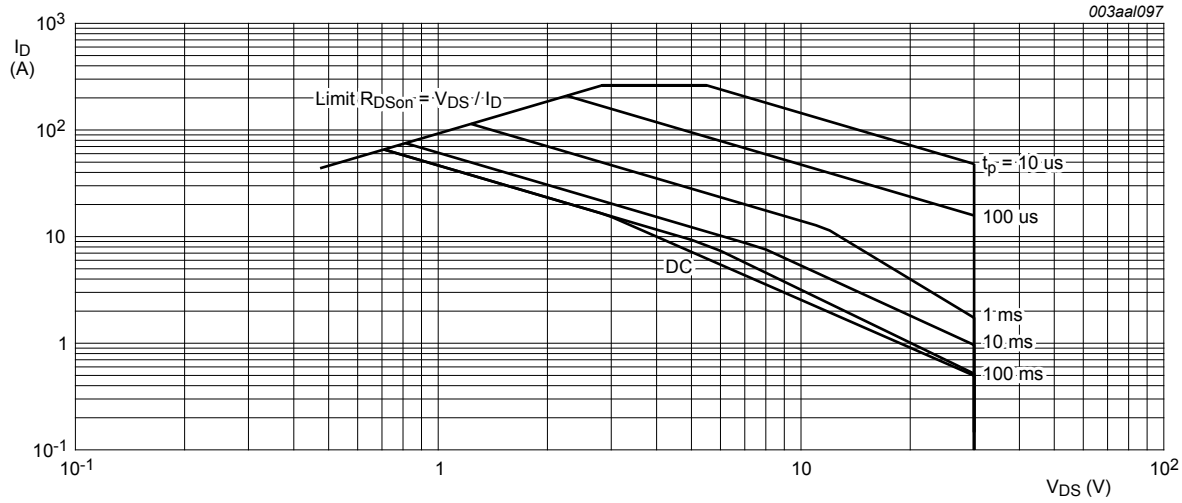



**Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage**

$$T_{mb} = 25°C;\ I_{DM} \text{ is a single pulse}$$

# 9. Thermal characteristics

**Table 6. Thermal characteristics**

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| $R_{th(j\text{-}mb)}$ | thermal resistance from junction to mounting base | Fig. 6 | | - | 3 | 3.22 | K/W |

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | Fig. 4 | | - | 50 | - | K/W |
| | | Fig. 5 | | - | 125 | - | K/W |

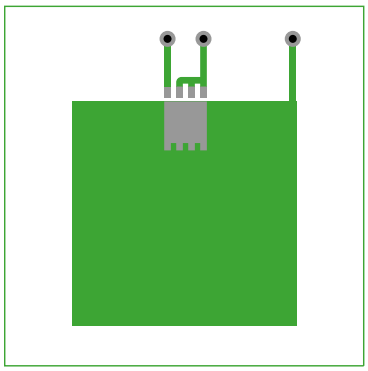



Fig. 4. PCB layout for thermal resistance junction to ambient 1” square pad; FR4 Board; 2oz copper

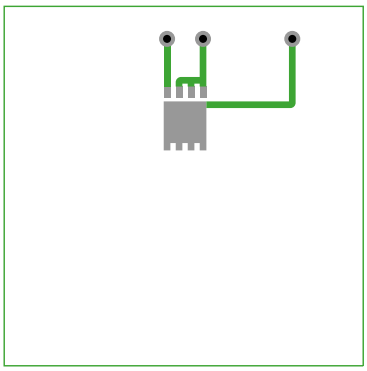



Fig. 5. PCB layout for thermal resistance junction to ambient minimum footprint; FR4 Board; 2oz copper

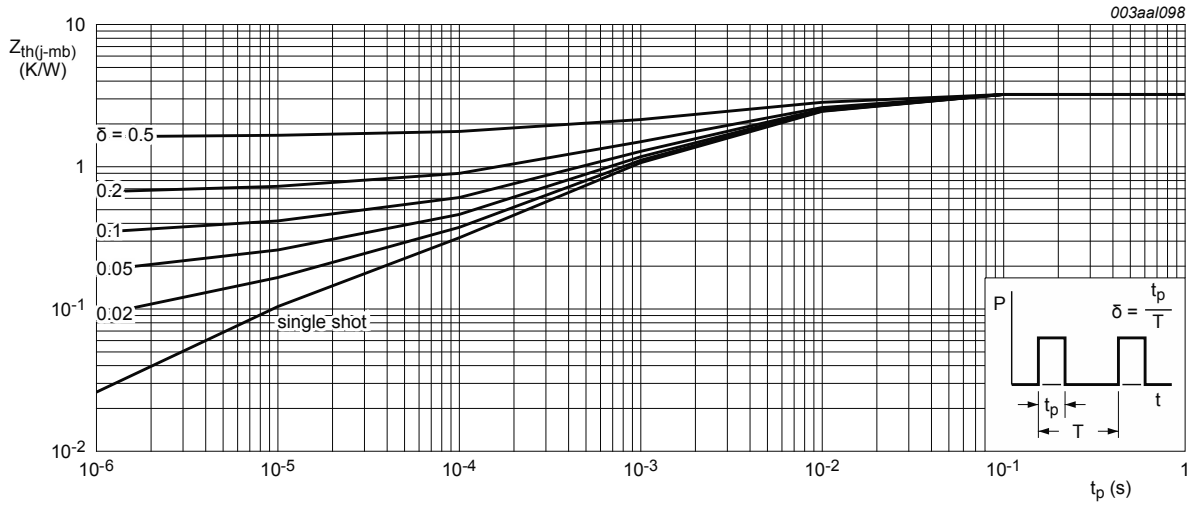



Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

# 10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| **Static characteristics** | | | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C | | 30 | - | - | V |
| | | $I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C | | 27 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$; $T_j$ = 25 °C | | 1.2 | 1.83 | 2.2 | V |

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| $\Delta V_{GS(th)}/\Delta T$ | gate-source threshold voltage variation with temperature | 25 °C ≤ $T_j$ ≤ 150 °C | | - | -4 | - | mV/K |
| $I_{DSS}$ | drain leakage current | $V_{DS}$ = 24 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C | | - | - | 1 | µA |
| | | $V_{DS}$ = 24 V; $V_{GS}$ = 0 V; $T_j$ = 150 °C | | - | - | 100 | µA |
| $I_{GSS}$ | gate leakage current | $V_{GS}$ = 16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C | | - | - | 100 | nA |
| | | $V_{GS}$ = -16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C | | - | - | 100 | nA |
| $R_{DSon}$ | drain-source on-state resistance | $V_{GS}$ = 4.5 V; $I_D$ = 15 A; $T_j$ = 25 °C; Fig. 10 | | - | 6.7 | 8.35 | mΩ |
| | | $V_{GS}$ = 4.5 V; $I_D$ = 15 A; $T_j$ = 150 °C; Fig. 11; Fig. 10 | | - | - | 13.8 | mΩ |
| | | $V_{GS}$ = 10 V; $I_D$ = 15 A; $T_j$ = 25 °C; Fig. 10 | | - | 5 | 6 | mΩ |
| | | $V_{GS}$ = 10 V; $I_D$ = 15 A; $T_j$ = 150 °C; Fig. 11; Fig. 10 | | - | - | 9.9 | mΩ |
| $R_G$ | gate resistance | f = 1 MHz | | - | 2.36 | - | Ω |
| **Dynamic characteristics** | | | | | | | |
| $Q_{G(tot)}$ | total gate charge | $I_D$ = 15 A; $V_{DS}$ = 15 V; $V_{GS}$ = 10 V; Fig. 12; Fig. 13 | | - | 13.7 | - | nC |
| | | $I_D$ = 15 A; $V_{DS}$ = 15 V; $V_{GS}$ = 4.5 V; Fig. 12; Fig. 13 | | - | 6.5 | - | nC |
| | | $I_D$ = 0 A; $V_{DS}$ = 0 V; $V_{GS}$ = 10 V | | - | 12.2 | - | nC |
| $Q_{GS}$ | gate-source charge | $I_D$ = 15 A; $V_{DS}$ = 15 V; $V_{GS}$ = 4.5 V; Fig. 12; Fig. 13 | | - | 1.7 | - | nC |
| $Q_{GS(th)}$ | pre-threshold gate-source charge | | | - | 1.2 | - | nC |
| $Q_{GS(th-pl)}$ | post-threshold gate-source charge | | | - | 0.5 | - | nC |
| $Q_{GD}$ | gate-drain charge | | | - | 1.8 | - | nC |
| $V_{GS(pl)}$ | gate-source plateau voltage | $I_D$ = 15 A; $V_{DS}$ = 15 V; Fig. 12; Fig. 13 | | - | 2.2 | - | V |
| $C_{iss}$ | input capacitance | $V_{DS}$ = 15 V; $V_{GS}$ = 0 V; f = 1 MHz; $T_j$ = 25 °C; Fig. 14 | | - | 832 | - | pF |
| $C_{oss}$ | output capacitance | | | - | 587 | - | pF |
| $C_{rss}$ | reverse transfer capacitance | | | - | 64 | - | pF |
| $t_{d(on)}$ | turn-on delay time | $V_{DS}$ = 15 V; $R_L$ = 1 Ω; $V_{GS}$ = 4.5 V; $R_{G(ext)}$ = 5 Ω | | - | 9 | - | ns |
| $t_r$ | rise time | | | - | 16.2 | - | ns |
| $t_{d(off)}$ | turn-off delay time | | | - | 10.5 | - | ns |
| $t_f$ | fall time | | | - | 10.9 | - | ns |

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| $Q_{oss}$ | output charge | $V_{GS}$ = 0 V; $V_{DS}$ = 15 V; f = 1 MHz; $T_j$ = 25 °C | | - | 11.5 | - | nC |
| **Source-drain diode** | | | | | | | |
| $V_{SD}$ | source-drain voltage | $I_S$ = 10 A; $V_{GS}$ = 0 V; $T_j$ = 25 °C; Fig. 15 | | - | 0.81 | 1.2 | V |
| $t_{rr}$ | reverse recovery time | $I_S$ = 15 A; $dI_S/dt$ = -100 A/µs; $V_{GS}$ = 0 V; $V_{DS}$ = 15 V; Fig. 16 | | - | 23.4 | - | ns |
| $Q_r$ | recovered charge | | [1] | - | 12.6 | - | nC |
| $t_a$ | reverse recovery rise time | | | - | 10.6 | - | ns |
| $t_b$ | reverse recovery fall time | | | - | 12.8 | - | ns |
| S | softness factor | | | - | 1.2 | - | |

[1] includes capacitive recovery

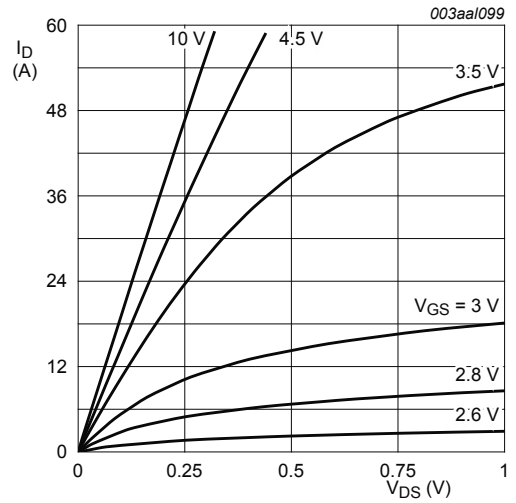



**Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values**

$T_j = 25°C$

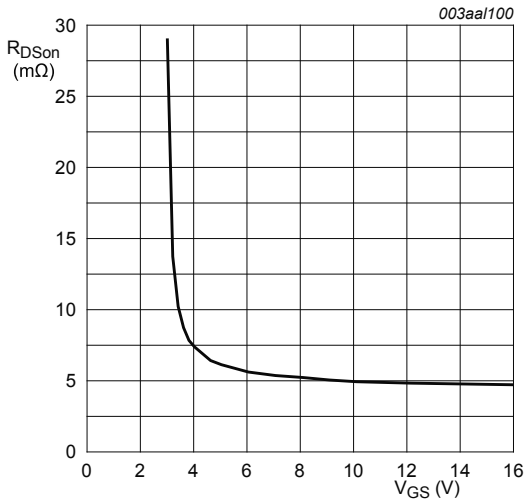



**Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values**

$T_j = 25°C;\ I_D = 15A$

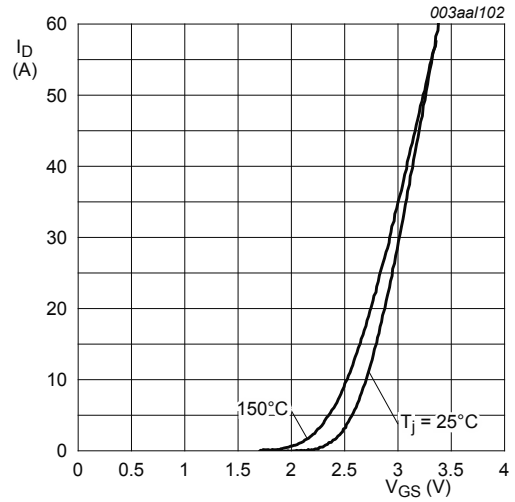



**Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values**

$V_{DS} = 12V$

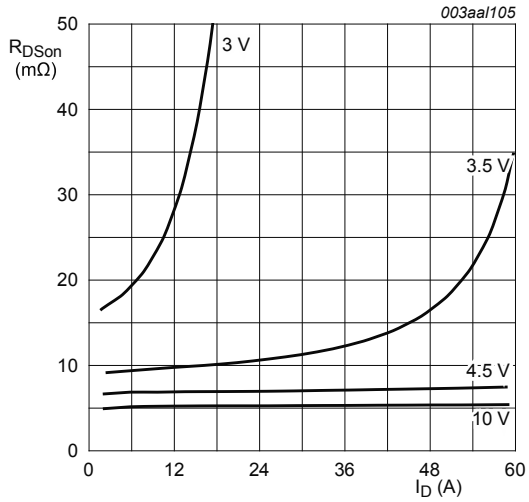



**Fig. 10. Drain-source on-state resistance as a function of drain current; typical values**

$T_j = 25°C$

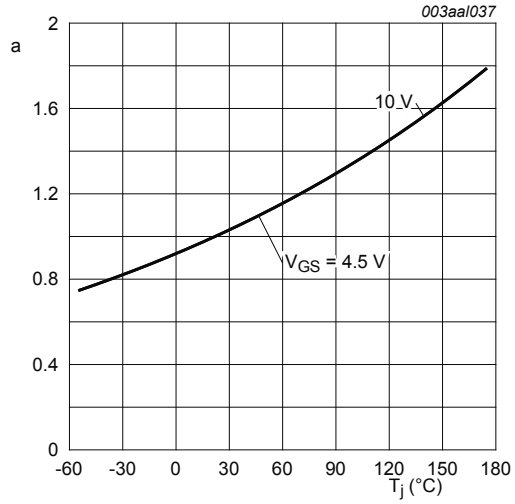



**Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature**

$$a = \frac{R_{DSon}}{R_{DSon\,(25°C)}}$$

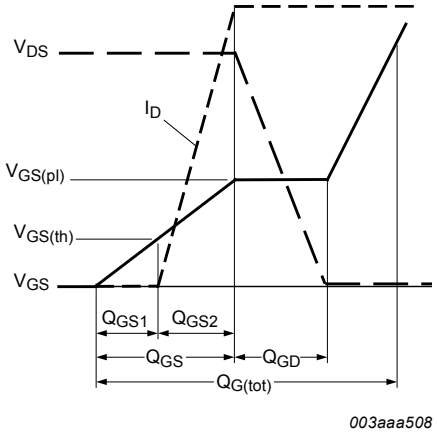



**Fig. 12. Gate charge waveform definitions**

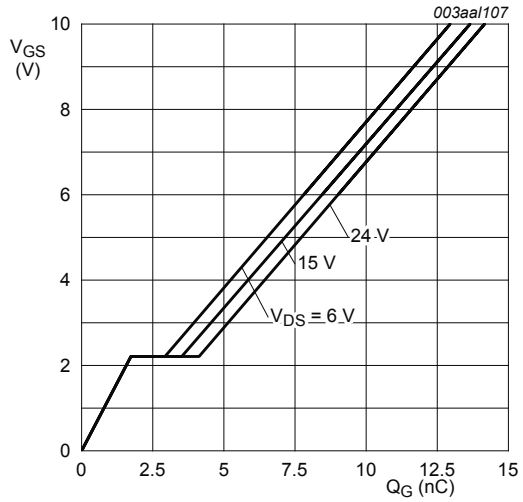



**Fig. 13. Gate-source voltage as a function of gate charge; typical values**

$T_j = 25°C;\ I_D = 15A$

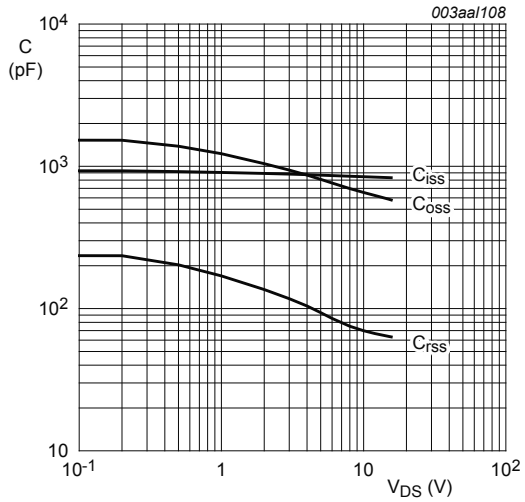



**Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**

$V_{GS} = 0V;\ f = 1MHz$

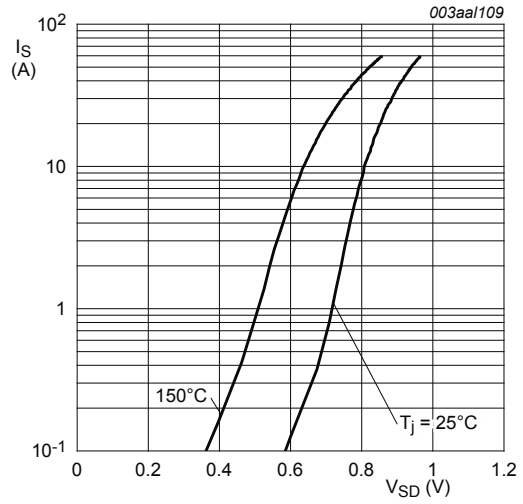



**Fig. 15. Source current as a function of source-drain voltage; typical values**

$V_{GS} = 0V$

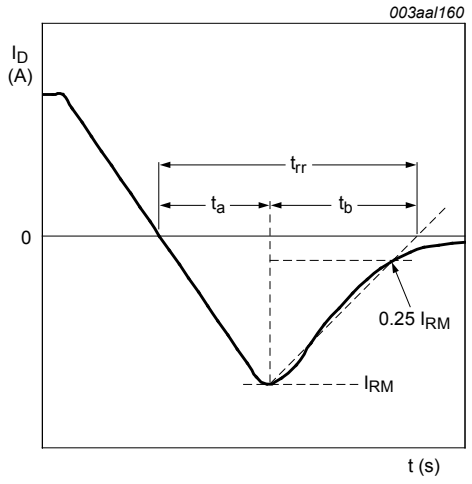
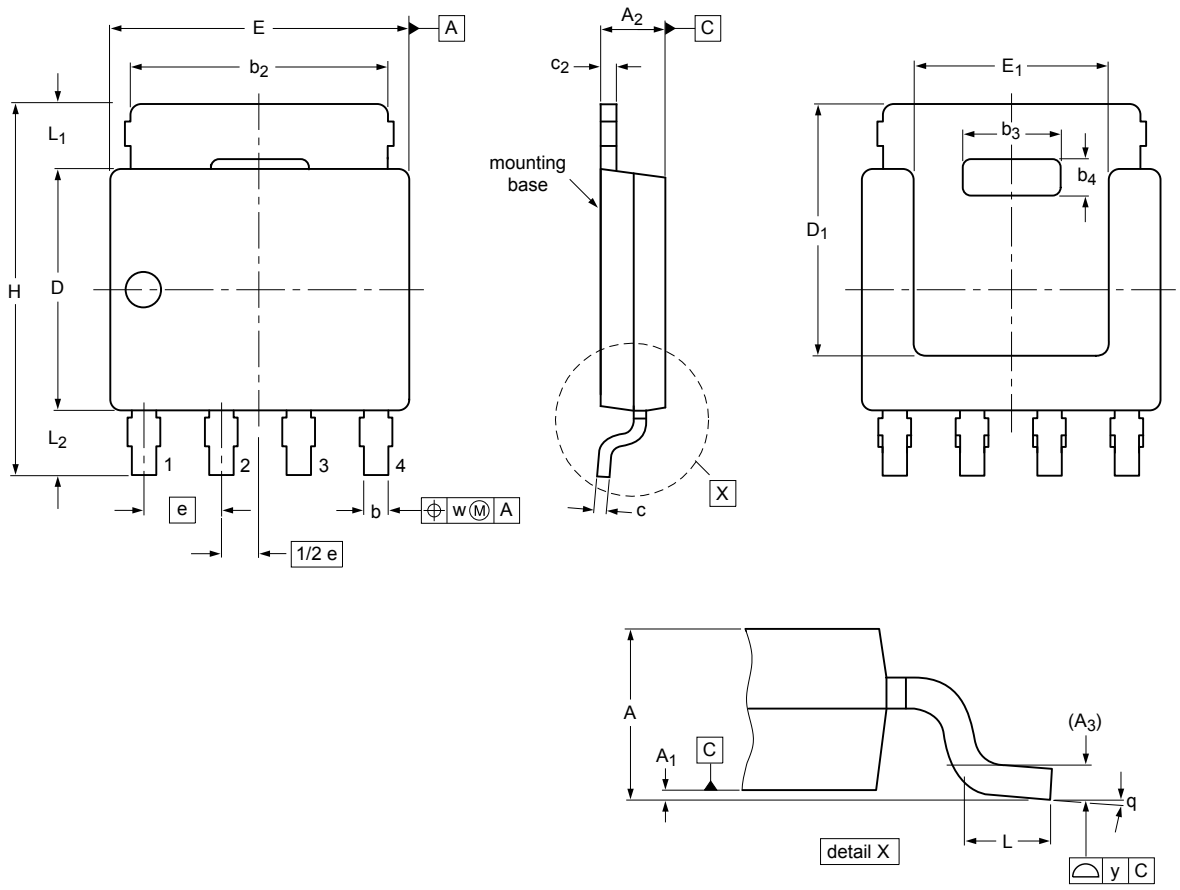



**Fig. 16. Reverse recovery timing definition**

# 11. Package outline

**Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads** **SOT669**




| θ |
|---|
| 8° |
| 0° |

Dimensions (mm are the original dimensions)

| Unit[1] | | A | $A_1$ | $A_2$ | $A_3$ | b | $b_2$ | $b_3$ | $b_4$ | c | $c_2$ | $D^{(1)}$ | $D_1{}^{(1)}$ | $E^{(1)}$ | $E_1{}^{(1)}$ | e | H | L | $L_1$ | $L_2$ | w | y |
|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|
| mm | max | 1.20 | 0.15 | 1.10 | | 0.50 | 4.41 | 2.2 | 0.9 | 0.25 | 0.30 | 4.10 | 4.20 | 5.0 | 3.3 | | 6.2 | 0.85 | 1.3 | 1.3 | | |
| | nom | | | | 0.25 | | | | | | | | | | | 1.27 | | | | | 0.25 | 0.1 |
| | min | 1.01 | 0.00 | 0.95 | | 0.35 | 3.62 | 2.0 | 0.7 | 0.19 | 0.24 | 3.80 | | 4.8 | 3.1 | | 5.8 | 0.40 | 0.8 | 0.8 | | |

Note
1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

*sot669_po*

| Outline version | References | | | | European projection | Issue date |
|---|---|---|---|---|---|---|
| | IEC | JEDEC | JEITA | | | |
| SOT669 | | MO-235 | | | | ~~11-03-25~~ 13-02-27 |

**Fig. 17. Package outline LFPAK56; Power-SO8 (SOT669)**

# 12. Legal information

## 12.1 Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|---|---|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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# 13. Contents





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